

# SEMI China CS Std. Technical Committee

## Silicon Carbide substrate Task Force



Zhang Jiaqi, 12/05/2024

**STANDARDS**

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## Leaders of Silicon Carbide substrate Task Force

No.	Name	Company	Industry Chain
1	陆敏	臻晶半导体	Silicon Carbide Industry
2	郑红军	臻晶半导体	Silicon Carbide Industry
3	闫方亮	米格实验室	Testing company

# Members of Silicon carbide substrate Task Force

No.	Name	Company	Industry Chain
1	赵然	粤海金	Substrate manufacturer
2	林健	中电科46所	Substrate R&D Institution
3	佘宗静	天科合达	Substrate manufacturer
4	钮应喜	中科院半导体所	Epitaxial production
5	冯淦	瀚天天成	Epitaxial production
6	唐为华	北京邮电大学	Substrate R&D Institution
7	孙聂枫	中电科13所	Substrate R&D Institution
8	Tom Barbieri	Wolfspeed	Substrate & Epi manufacturer
9	刘国友	株洲中车时代电气	Device manufacturing
10	刘建哲	浙江博蓝特	Substrate manufacturer
11	窦文涛	山东天岳	Substrate manufacturer
12	赵丽丽	科友半导体	Substrate manufacturer
13	侯晓蕊	山西烁科	Substrate manufacturer
14	李玲	国家电网	Device manufacturing
15	唐军	中电化合物	Substrate & Epi manufacturer

# Members of Silicon carbide substrate Task Force

No.	Name	Company	Industry Chain
16	邓小川	电子科大	Device R&D Institution
17	Masayoshi Obara	Shinetsu Handotai	Substrate & Epi manufacturer
18	Toshimasa Yamamoto	DENSO	Device manufacturing
19	贾怀宇	三禾泰达	Equipment manufacturer
20	顾伟中	瑞霏光电	Equipment manufacturer
21	李国平	江苏卓远半导体有限公司	Equipment manufacturer
22	赵华利	河北同光半导体股份有限公司	Substrate manufacturer
23	Yoshise	日本	Substrate R&D Institution
12/5/2024			4

## Documents in Work

No.	Project number	Doc. Name	Proposed Company
1	6767	TEST METHOD FOR GBIR, SBIR, SFQR and SORI OF SILICON CARBIDE WAFERS BY OBLIQUE INCIDENT INTERFERENCE METHOD 碳化硅平整度的光学干涉测量方法	臻晶半导体
2	6769B	TEST METHOD FOR RESIDUAL STRESS OF SILICON CARBIDE WAFERS BY PHOTOELASTIC 碳化硅应力的光弹效应测量方法	臻晶半导体

# Specific work (具体工作)

Based on committee recommendations on the Spring Meeting 2024

No.	Date	Task	Result
1	Jun. 12, 2024	SEMI Standards Compound Semiconductor China TC Chapter Meeting Spring 2024 SEMI化合物半导体标委会春季会议	简要汇报沟通进展，继续与国外专家沟通
2	Jun. 12, 2024--Now	Communicate with the foreign experts who give their opinions, and complete the revision of the 6769B standard 与提出意见的国外专家沟通，完成6769B标准的修订	解决了绝大部分问题，尚有几个细节问题需要再沟通确认
3	Now--China Spring Standards Meeting 2025	Submit a request for extension, continue to communicate with foreign experts, and complete the revisions of standards 6767 and 6769B 提出延期申请，继续与国外专家沟通，完成6767标准和6769B标准的修改	与所有专家达成一致意见

## Extension Request (延期申请)

**We believe that these two standards are very significant for the inspection work of silicon carbide substrates. As we have exceeded the deadline, we hope to apply for one-year extension. We will expedite our progress to refine the content of the standards as soon as possible.**

**我们认为这两项标准对碳化硅衬底的检测工作来说很有意义。由于超过时限，所以希望申请延期一年。我们将加快进度，尽早完善标准的内容。**

**6767: There are significant opinions from foreign experts, and more communication is needed to resolve all doubts.**

**6767: 国外专家意见较大，需要多进行沟通来解决所有的疑问。**

**6769B: Further communication with foreign experts is needed on some detailed issues to resolve all doubts.**

**6769B: 在一些细节问题上还要再与国外专家沟通，解决所有的疑问。**

# Change the title of 6769B

**Add "EFFECT" at the end of the original title to make the meaning more precise.**

**(在原标题末尾增加“EFFECT”，使语意表达更准确)**

**Original title: TEST METHOD FOR RESIDUAL STRESS OF SILICON CARBIDE  
WAFERS BY PHOTOELASTIC**

**Current Title: TEST METHOD FOR RESIDUAL STRESS OF SILICON CARBIDE  
WAFERS BY PHOTOELASTIC EFFECT**





**THANK YOU**

**STANDARDS**